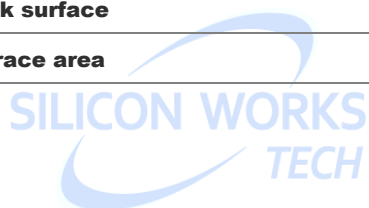




睿晶科技股份有限公司
SILICON WORKS TECH CORPORATION

B SOI SPEC

Growth method	Cz, MCz,
Diameter	200 mm, 150 mm
Crystal orientation	<100>,<111>
N type dopants	Antimony, Phosphorus, Arsenic
P type dopants	Boron
Resistivity	From 0.0008 to 100 Ohm-cm
Device layer thickness	From 0.3 μm to 305 μm
	Tolerance $\pm 0.3 \mu\text{m}$ (BSOI)
Buried oxide layer thickness	From 0.1 μm to 6 μm
Handle wafer thickness	200 mm: 400 μm to 1000 μm
	150 mm: 400 μm to 1000 μm
Back surface	Polished or etched
Terrace area	Standard or Terrace Free



睿晶科技股份有限公司
SILICON WORKS TECH CORPORATION